

**Preliminary Amendment**

Applicant: Thomas Hecht et al.

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Title: METHOD AND PROCESS REACTOR FOR SEQUENTIAL GAS PHASE DEPOSITION BY MEANS OF A PROCESS CHAMBER AND AN AUXILIARY CHAMBER (As Amended)

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**IN THE ABSTRACT**

Please replace the Abstract with the following rewritten paragraph:

~~Abstract~~

**METHOD AND PROCESS REACTOR FOR SEQUENTIAL GAS PHASE  
DEPOSITION BY MEANS OF A PROCESS CHAMBER AND AN AUXILIARY  
CHAMBER**

**Abstract**

In a process chamber ~~(10)~~ of a process reactor ~~(1)~~, a sequential gas phase deposition (ALD, atomic layer deposition) of two or more precursors fed in by means of process gases is controlled. T, the process chamber ~~(10)~~ being ~~is~~ connected to an auxiliary chamber ~~(20)~~ for a change of precursor and so the precursor to be removed is rarefied in the process chamber ~~(10)~~, so that a process duration of the sequential gas phase deposition that is determined by a change of precursor is reduced.

~~(Figure 1)~~